Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/758,871
				Filing Date	January 16, 2004
				First Named Inventor	Sheppard et al.
				Group Art Unit	~~2815~~ 2812
(use as many sheets as necessary)				Examiner Name	~~N. Drew Richards~~ GEYER, S.
Sheet	1	of	1	Attorney Docket Number	5308-291

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U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
SBG	1.	US-5,990,531		Taskar et al.	11-23-1999
SBG	2.	US-5,389,571		Takeuchi et al.	02-14-1995
SBG	3.	US-2003/0145784		Thompson et al.	08-07-2003
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OTHER NON PATENT LITERATURE DOCUMENTS			
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				First Named Inventor	Scott Sheppard
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Examiner Signature	KSG	Date Considered	12-8-05

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				Filing Date	January 16, 2004
				First Named Inventor	Sheppard et al.
				Group Art Unit	~~2815~~ 2812
(use as many sheets as necessary)				Examiner Name	~~Richards, N. Drew~~ GEYER, S.
Sheet	3	of	3	Attorney Docket Number	5308-291

OTHER NON PATENT LITERATURE DOCUMENTS			
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SBG	42.	United States Patent Application entitled "Composite Substrates of Conductive And Insulating or Semi-Insulating Group III-Nitrides For Group III-Nitride Devices," Serial No. 11/103,127, filed April 11, 2005 (Attorney Docket No. 5308-551).	
SBG	43.	United States Patent Application entitled "Thick Semi-Insulating or Insulating Epitaxial Gallium Nitride Layers and Devices Incorporating Same," Serial No. 11/103,117, filed April 11, 2005 (Attorney Docket No. 5308-553).	
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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Applicant: Sheppard et al.	
	Filing Date: January 16, 2004	GAU: ~~2815~~ 2812

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Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
SBG	1.	5,592,501	1/7/97	Edmond et al.	372	45	

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Examiner: KBG Date Considered: 12-8-05

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Substitute form 1449A/PTO	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/758,871
	Filing Date	January 16, 2004
	First Named Inventor	Sheppard
	Group Art Unit	~~2811~~ 2812
(use as many sheets as necessary)	Examiner Name	~~Tom Thomas~~ Geyer, J.
Sheet A2 of A3	Attorney Docket Number	5308-291

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